

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) :	Haining S. YANG	Group Art Unit:	2813
Appln. No. :	10/707,841	Examiner:	Chen, Jack S.J.
Filed :	January 16, 2004	Confirmation No.:	1840
For :	METHOD AND STRUCTURE FOR CONTROLLING STRESS IN A TRANSISTOR CHANNEL		

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop Amendment
Randolph Building
401 Dulany Street
Alexandria, VA 22314

Sir :

SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with Applicants' duty of disclosure under 37 C.F.R. §1.56, and pursuant to the provisions of 37 C.F.R. §§1.97 and 1.98, and supplemental to the Information Disclosure Statements filed on January 20, 2004, and August 23, 2005, Applicant hereby directs the Examiner's attention to the documents listed on the enclosed copy of the PTO-1449 Form.

Copies of the cited foreign patent documents and non-patent literature are being submitted herewith. However, pursuant to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. 1.98 (a)(2)(i), copies of the cited U.S. patents and U.S. published patent applications are not enclosed herewith. If any copies are needed, the Examiner is respectfully requested to contact the undersigned.

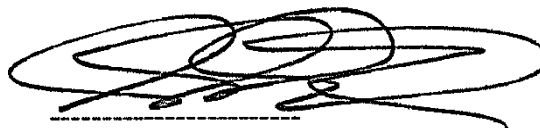
Applicant respectfully requests that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

Applicant notes that while this Supplemental Information Disclosure Statement is being filed more than three months from the filing date, Applicant has not received a first action on the merits from the U.S. Patent and Trademark Office. Accordingly, consideration of the enclosed document is required under 37 C.F.R. 1.97(b)(3).

However, if the first action on the merit has been mailed prior to the filing date of this Supplemental Information Disclosure Statement, Applicant hereby authorizes the Commissioner to charge any fees necessary to ensure consideration of the documents cited herein to International Business Machines Deposit Account No. 09-0458.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,
Haining S. YANG

A handwritten signature in black ink, appearing to read 'Andrew M. Calderon', is written over a horizontal dashed line.

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FORM PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. P27160	Application No. 10/707,841
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Haining S. YANG	
		Filing Date January 16, 2004	Group 2813

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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		JP 64-76755	3-22-1989	Japan			X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27160	Application No. 10/707,841		
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				Filing Date January 16, 2004	Group 2813		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
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